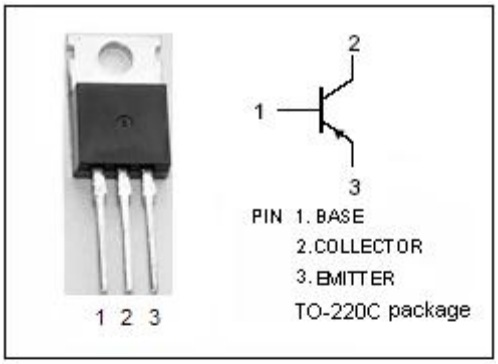
isc Silicon PNP Power Transistor BD224

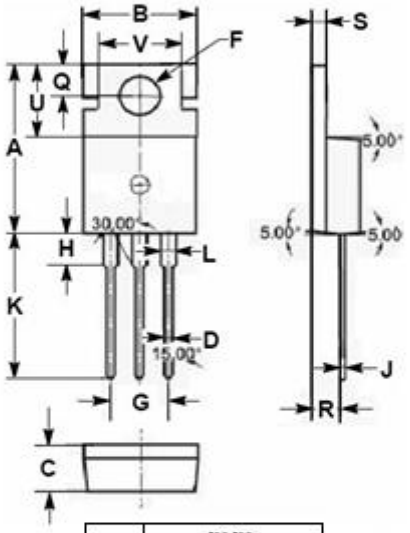


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -40V(Min)
- DC Current Gain -h_{FE} =30(Min)@ I_C= -0.3A
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in general purpose power amplifier and switching applications.



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-6	A
P_C	Collector Power Dissipation @ T_C=25℃	36	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -30mA ; I_B= 0	-40			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -1A			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -4A ; V_{CE}= -4V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V ; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-100	μA
h_{FE-1}	DC Current Gain	I_C= -0.3A ; V_{CE}= -4V	30		120	
h_{FE-2}	DC Current Gain	I_C= -4A ; V_{CE}= -4V	15			
f_T	Current-Gain—Bandwidth Product	I_C=-1A ; V_{CE}= -5V	3			MHz